

LPS25H

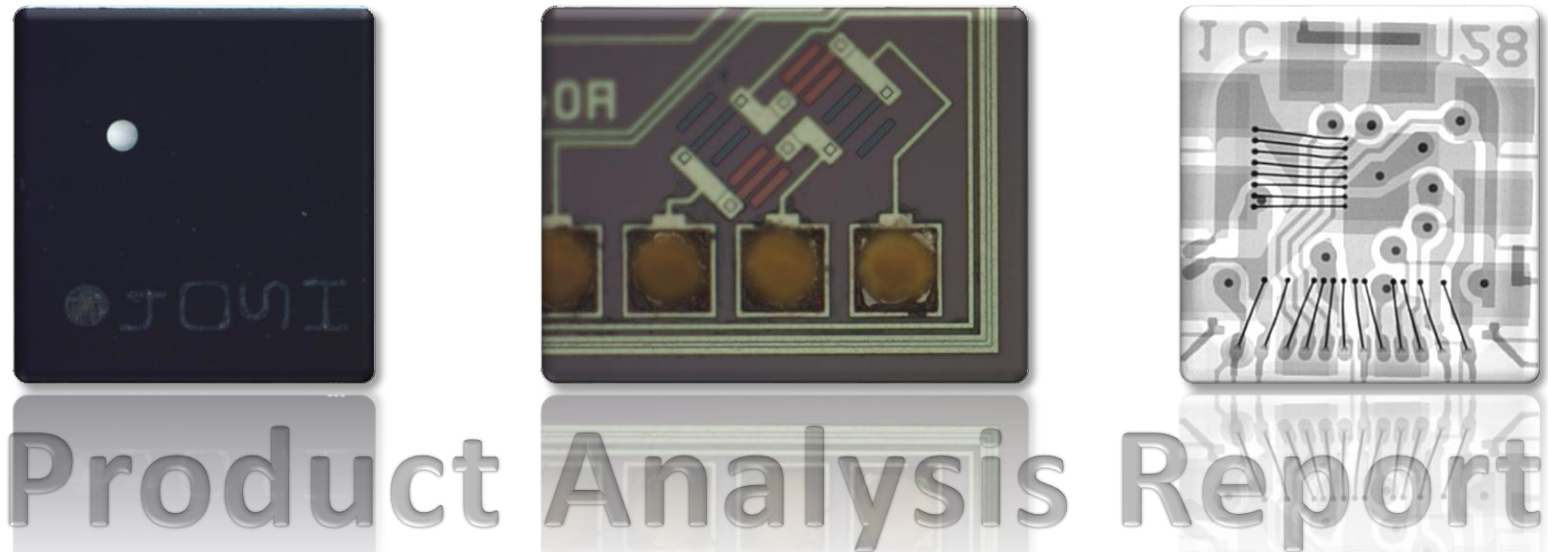
MEMS Pressure Sensor: 260-1260 hPa Absolute Digital output Barometer

www.sitrigroup.com

Weibo



Wechat



This report is protected by copyright and may not be by way of trade or otherwise, be copied, reproduced, re-sold, lent, hired out in any form without express written permission from Shanghai Industrial μ Technology Research Institute (Hereinafter referred to as SITRI). SITRI always endeavors to provide accurate and reliable information to its customers. However, it is not possible to guarantee absolute accuracy of all information contained herein and SITRI can assume no liability for inadvertent errors in this report.

This report was prepared for our Clients' private study, analysis or research and for no other purpose. The information contained in this report may describe technical innovations, which are the subject of patents held by third parties. The disclosure by SITRI of any such information is in no form whatsoever an inducement to infringe any patent. SITRI assumes no liability for patent infringement arising from the use of the information contained in this report.

To Know



- Device Summary.....3
 - Device Summary
- Package Overview5
 - Top Bottom Side View with Measurement
- ASIC Die Information.....7
 - Die Photo with Measurement
 - Die Mark
 - Die Corner Image
 - Pad Size
- ASIC Die General Structure.....11
 - Die Thickness
 - Each Layer Structure and Thickness Measurement
 - Gate Length of Poly Gate

- Pressure Sensor Die Information.....16
 - Die Photo with Measurement
 - Die Mark
 - Die Corner Image
 - Pad Size
- Piezoresistor Plan View20
 - Poly Stained of Piezoresistor OM and SEM View
- Piezoresistor Cross Section26
 - SEM Image and Measurement of Cross Section of Piezoresistor
 - Thickness of Cavity and Membrane
 - Measurement of P+ Doping and Poly Layer
- Major Findings35
 - Piezoresistor Principle
 - MEMS Pressure Sensor Process Flow
 - Summary of LPS25H